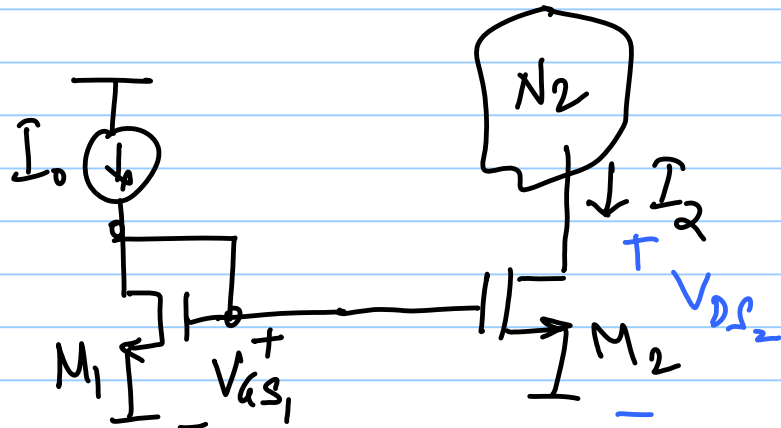


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Lec 10

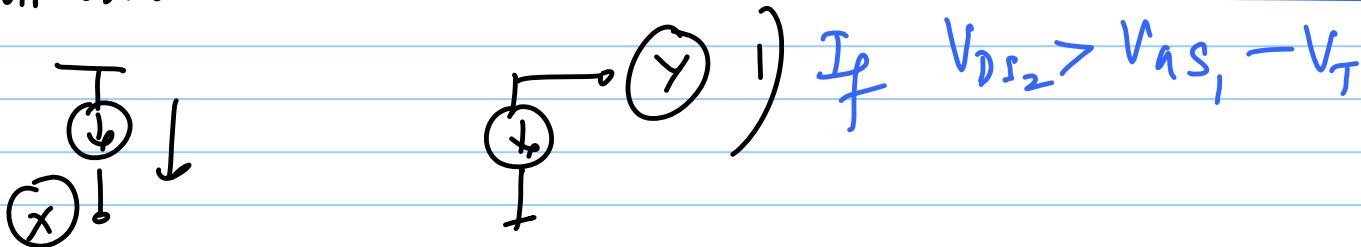


"Current Mirror"

$$I_{D1} = I_0$$

$$V_{gs1} = \sqrt{\frac{2I_0}{\mu_n C_{ox} \left(\frac{W}{L}\right)_1}} + V_T$$

$$I_{D2} = \frac{1}{2} \mu_n C_{ox} \left(\frac{W}{L}\right)_2 (V_{gs1} - V_T)^2$$



2) $\lambda \neq 0$

$$I_0 = I_{D1} = \frac{1}{2} \mu_n C_{ox} \left(\frac{W}{L} \right)_1 (V_{GS1} - V_T)^2 (1 + \lambda V_{DS1})$$

$\nearrow V_{GS1}$

$$I_{D2} = \frac{1}{2} \mu_n C_{ox} \left(\frac{W}{L} \right)_2 (V_{GS1} - V_T)^2 (1 + \lambda V_{DS2}) \quad ?$$

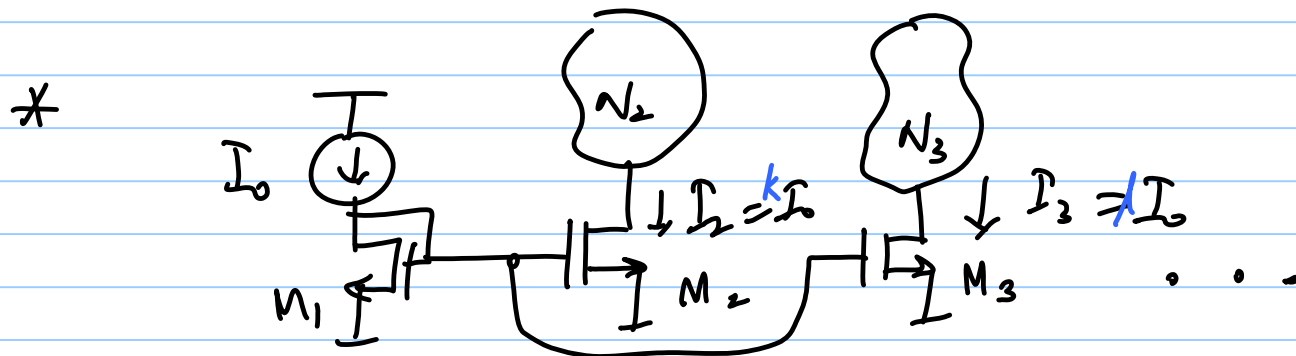
$$I_{D2} \neq I_0$$

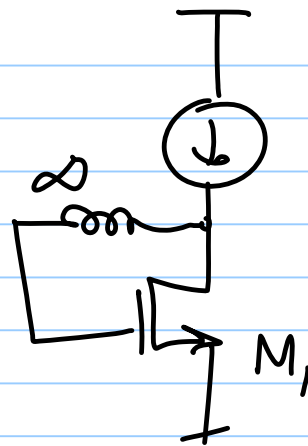
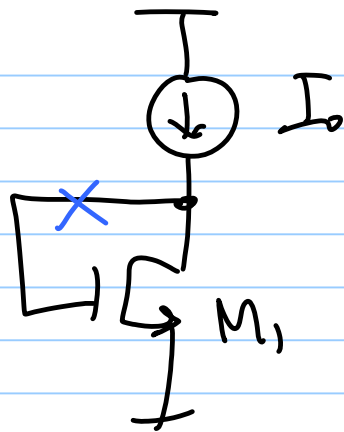
$$I_f \quad V_{DS2} > V_{GS1}, \quad I_{D2} = I_0 + \delta I$$

$$V_{DS2} < V_{GS1}, \quad I_{D2} = I_0 - \delta I$$

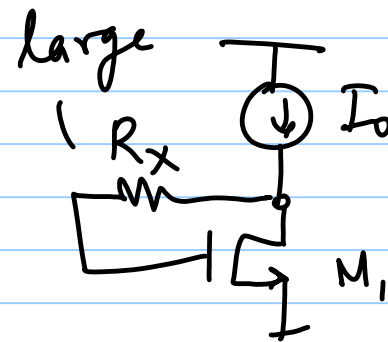
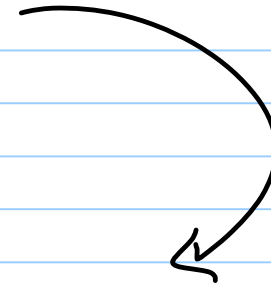
for small δI , we want small λ
 $\Rightarrow$ long devices ($\uparrow L_{1,2}$)

$$\left. \begin{aligned} * \quad L_2 &= L_1 \\ W_2 &= \frac{2}{n} W_1 \end{aligned} \right) \quad \mathbb{I}_{D_2} \approx \frac{2}{n} \mathbb{I}_0$$





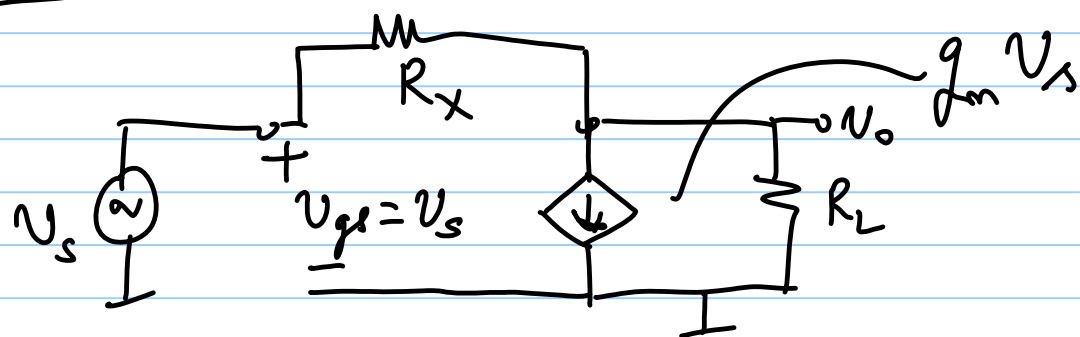
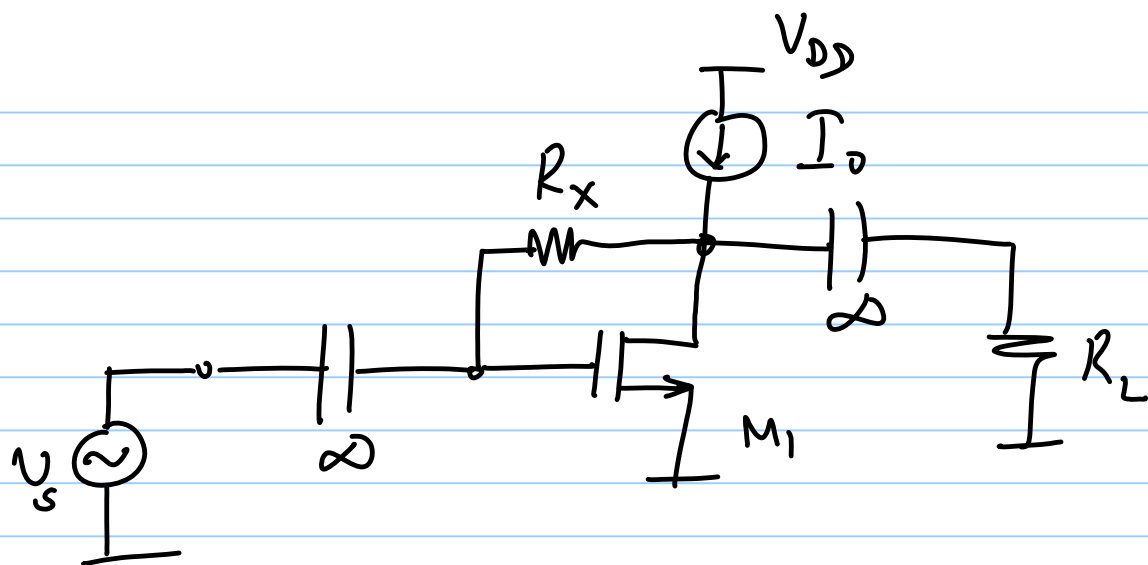
$$\hat{I} = 0 \quad \equiv \quad I = 0$$



$$V_{GS_1} = V_{DS_1}$$

$$I_{R_x} = 0$$

$$I_{D_1} = I_D$$



$$\frac{v_o}{v_s} = ?$$

KCL @ drain:

$$\frac{v_o}{R_L} + g_m v_s + \frac{(v_o - v_s)}{R_x} = 0$$

$$v_o \cdot g_L + g_m v_s + g_x v_o - g_x v_s = 0$$

$$\frac{v_o}{v_s} = \left(\frac{g_x - g_m}{g_x + g_L} \right)$$

We want $\frac{V_o}{V_s} = -\frac{g_m}{g_L} = -g_m R_L$

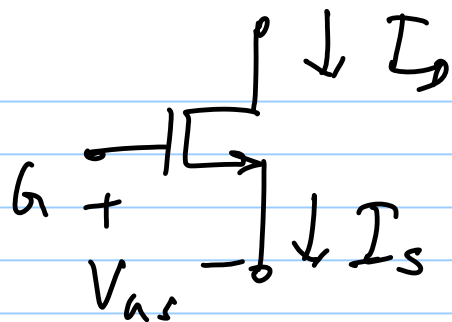
- $\therefore$ 1) $g_x \ll g_m$ more significant
2) $g_x \ll g_L$ ←
i.e. $R_x \gg R_L$

* This Circuit will potentially have lower ^{node} swing limit compared to the original amplifier

* Cut off limit $|V_A| = \frac{I_D}{g_m}$ remains the same

Negative fb.

So far: measured I_D
compared to I_0
drove V_A so that $I_D = I_0$



$$I_D = f(V_{gs})$$

both can
be tested

$$1) I_a = 0 \Rightarrow I_D = I_S$$

2) change V_a w V_s

$\swarrow$ keep V_s constant
 $\searrow$ keep V_a constant

$\Rightarrow$ 4 ways of biasing the transistor using negative f.b.